

N-channel 600 V, 0.550  $\Omega$  typ., 7.5 A MDmesh II Plus™ low  $Q_g$   
Power MOSFETs in D<sup>2</sup>PAK, DPAK, TO-220 and IPAK packages

Datasheet – production data

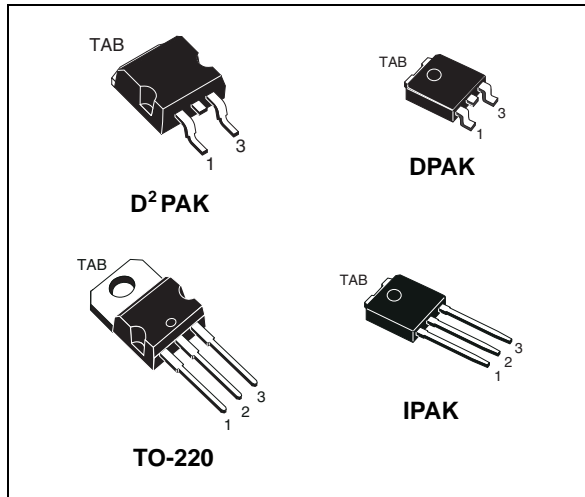
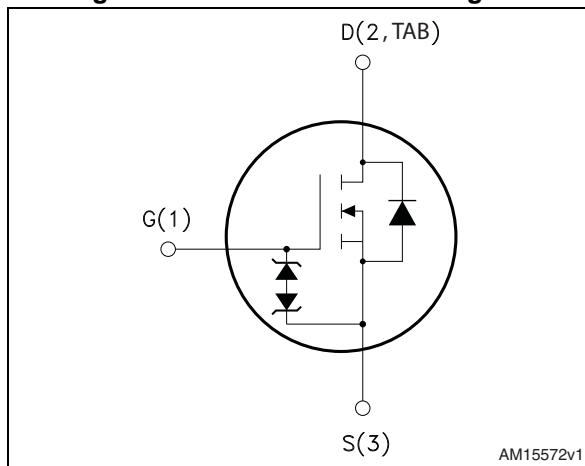


Figure 1. Internal schematic diagram



## Features

Order codes	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	$I_D$
STB10N60M2	650 V	0.600 $\Omega$	7.5 A
STD10N60M2			
STP10N60M2			
STU10N60M2			

- Extremely low gate charge
- Lower  $R_{DS(on)}$  x area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using a new generation of MDmesh™ technology: MDmesh II Plus™ low  $Q_g$ . These revolutionary Power MOSFETs associate a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. They are therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB10N60M2	10N60M2	D <sup>2</sup> PAK	Tape and reel
STD10N60M2		DPAK	
STP10N60M2		TO-220	Tube
STU10N60M2		IPAK	

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	7.5	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4.9	A
$I_{DM}^{(1)}$	Drain current (pulsed)	30	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	85	W
$dv/dt^{(1)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(2)}$	MOSFET $dv/dt$ ruggedness	50	
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature		

1.  $I_{SD} \leq 7.5\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ,  $V_{DD}=400\text{ V}$

2.  $V_{DS} \leq 480\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		D <sup>2</sup> PAK	DPAK	TO-220	I <sup>2</sup> PAK	
$R_{thj-case}$	Thermal resistance junction-case max	1.47				$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max <sup>(1)</sup>	30	50			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max			62.5	100	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz copper board

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	2.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$ , $I_D=I_{AR}$ ; $V_{DD}=50$ )	110	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$		0.550	0.600	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	400	-	pF
$C_{oss}$	Output capacitance		-	22	-	pF
$C_{riss}$	Reverse transfer capacitance		-	0.84	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$ , $V_{GS} = 0$	-	83	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	6.4	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 7.5\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	13.5	-	nC
$Q_{gs}$	Gate-source charge		-	2.1	-	nC
$Q_{gd}$	Gate-drain charge		-	7.2	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 3.75\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> and <a href="#">Figure 21</a> )	-	8.8	-	ns
$t_r$	Rise time		-	8	-	ns
$t_{d(off)}$	Turn-off delay time		-	32.5	-	ns
$t_f$	Fall time		-	13.2	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		7.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		30	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 7.5 \text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 7.5 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 18</a> )	-	270		ns
$Q_{rr}$	Reverse recovery charge		-	2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	14.4		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 7.5 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 18</a> )	-	376		ns
$Q_{rr}$	Reverse recovery charge		-	2.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	15		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK and IPAQ

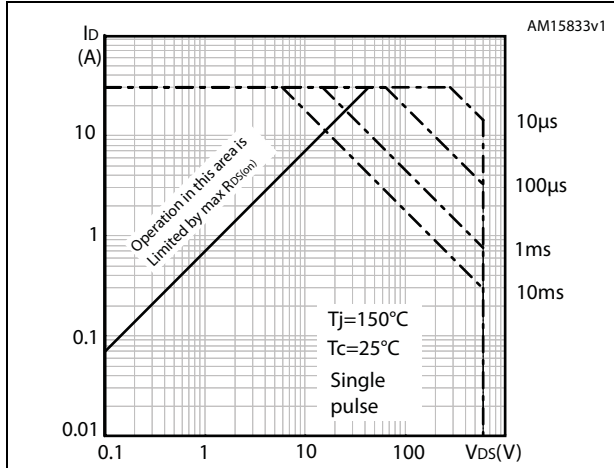


Figure 3. Thermal impedance for DPAK and IPAQ

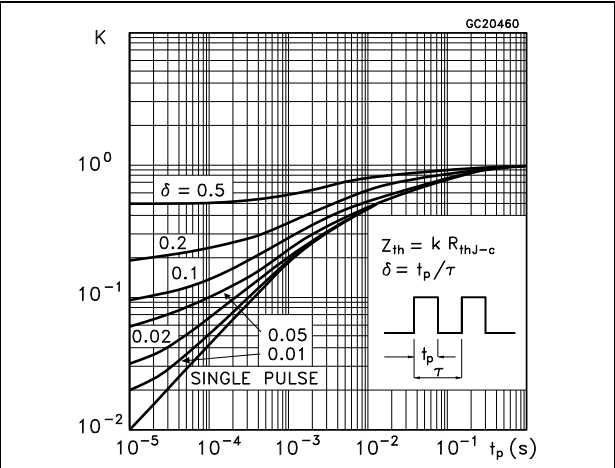


Figure 4. Safe operating area for D<sup>2</sup>PAK and TO-220

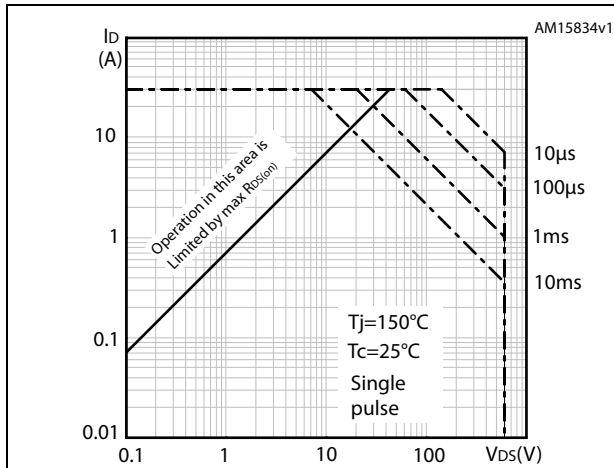


Figure 5. Thermal impedance for D<sup>2</sup>PAK and TO-220

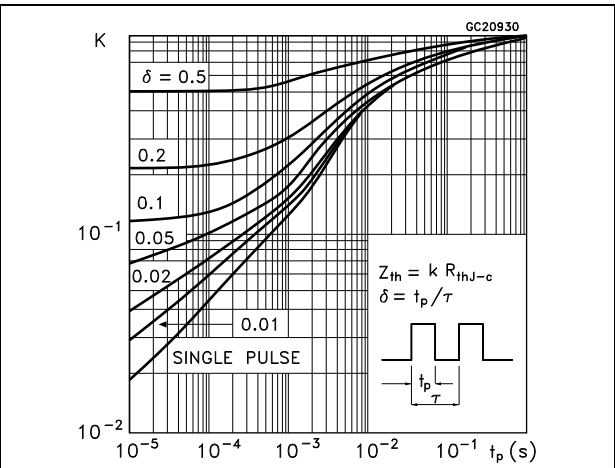


Figure 6. Output characteristics

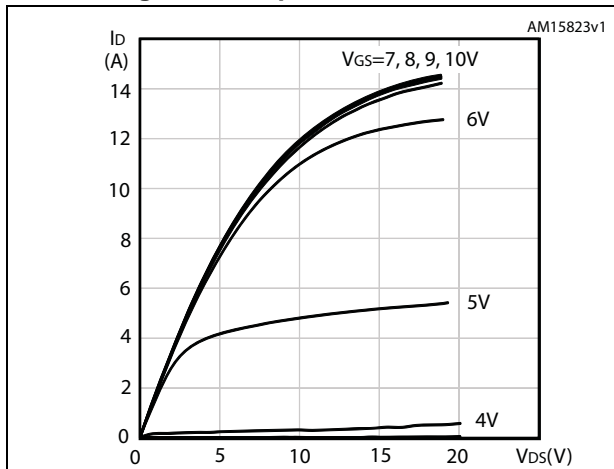


Figure 7. Transfer characteristics

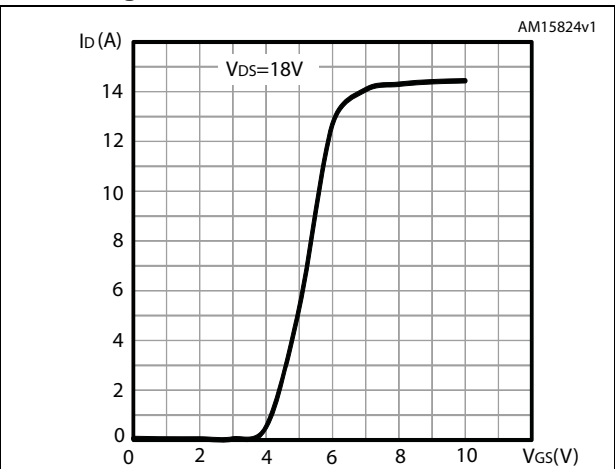


Figure 8. Gate charge vs gate-source voltage

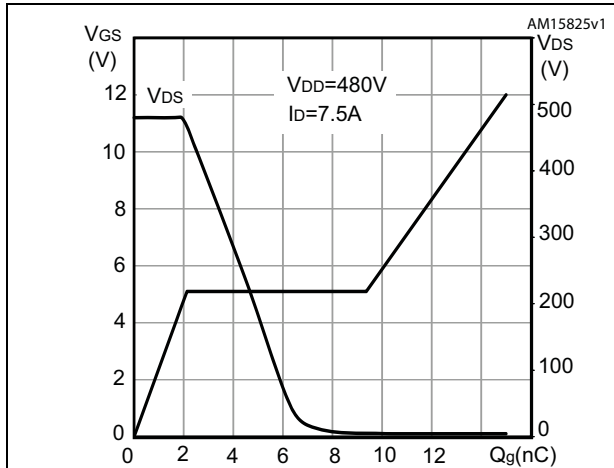


Figure 9. Static drain-source on-resistance

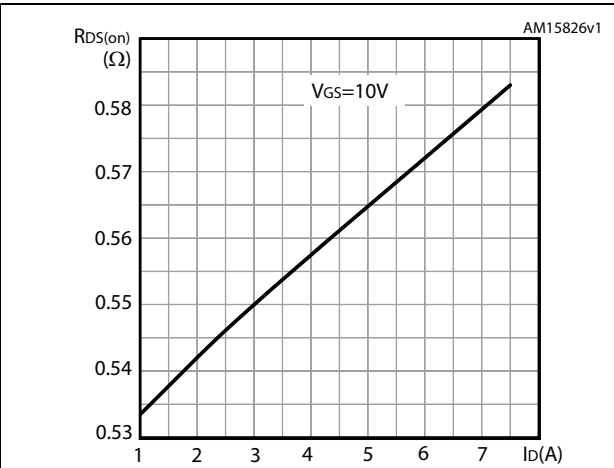


Figure 10. Capacitance variations

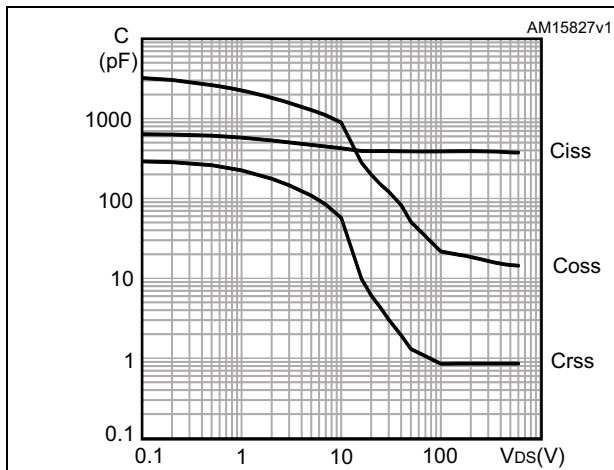


Figure 11. Normalized gate threshold voltage vs. temperature

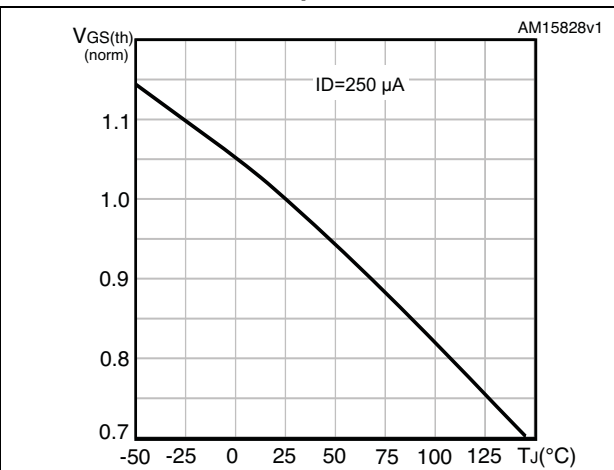


Figure 12. Normalized on-resistance vs temperature

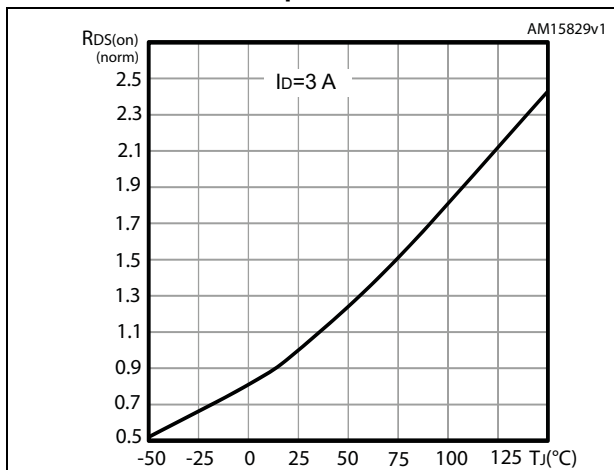


Figure 13. Source-drain diode forward characteristics

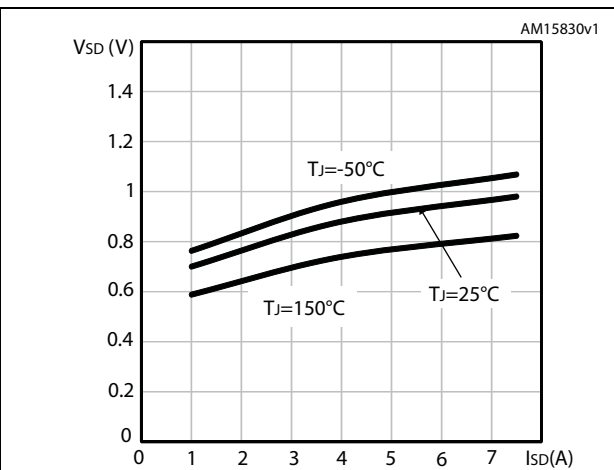


Figure 14. Normalized  $V_{DS}$  vs temperature

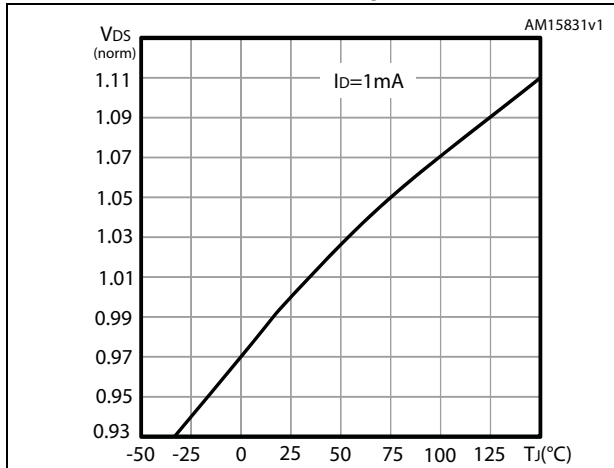
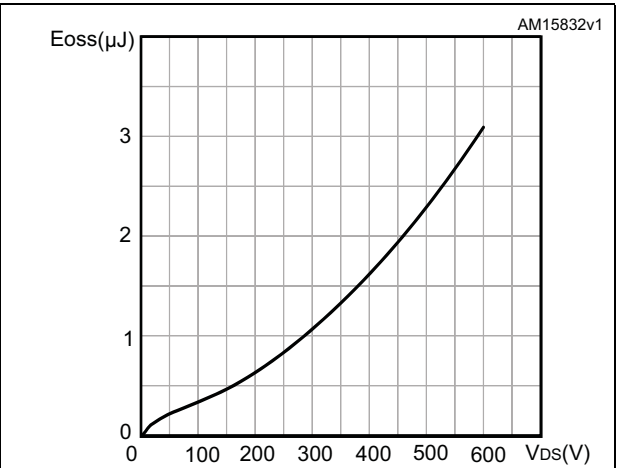


Figure 15. Output capacitance stored energy





### 3 Test circuits

Figure 16. Switching times test circuit for resistive load



Figure 17. Gate charge test circuit

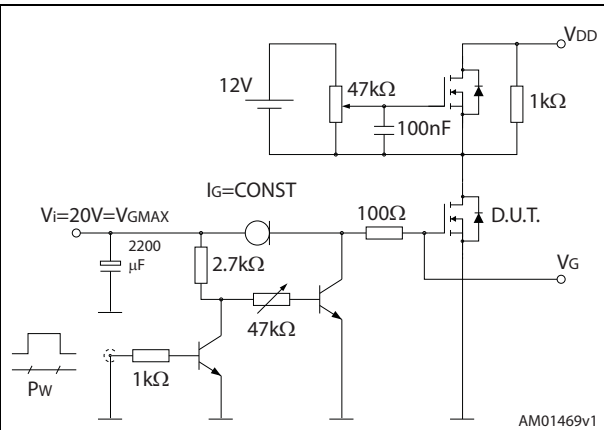


Figure 18. Test circuit for inductive load switching and diode recovery times

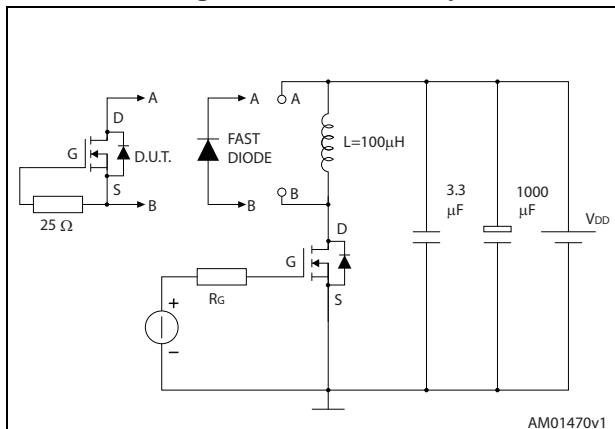


Figure 19. Unclamped inductive load test circuit

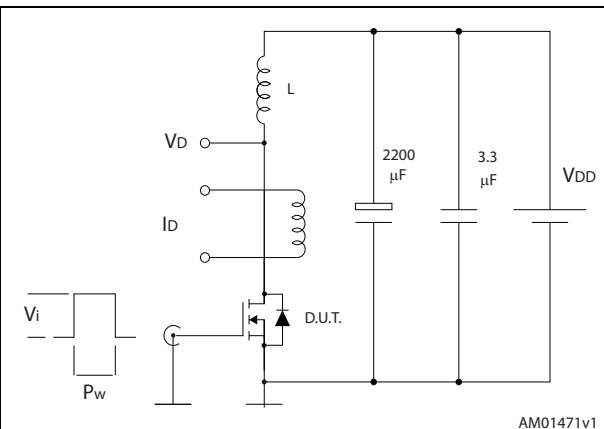


Figure 20. Unclamped inductive waveform

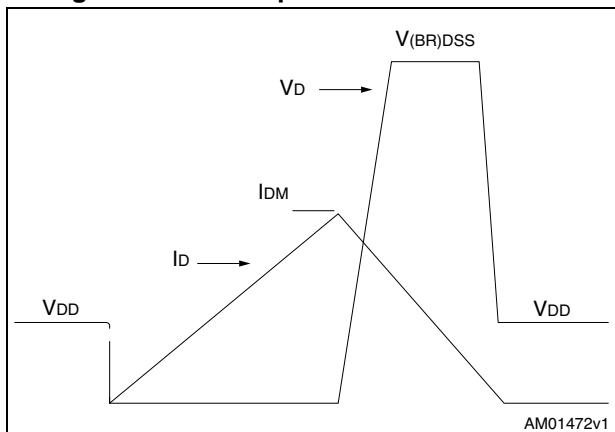
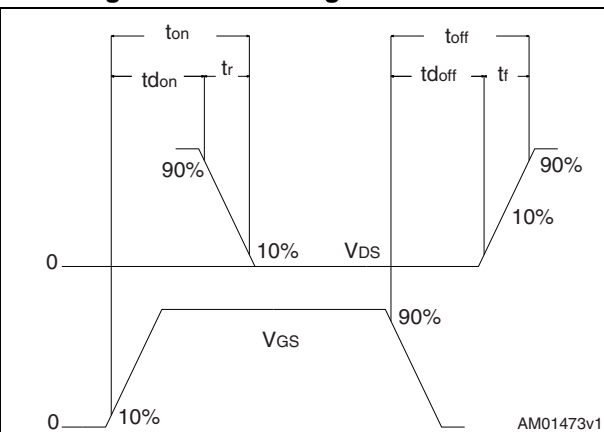


Figure 21. Switching time waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. D<sup>2</sup>PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22. D<sup>2</sup>PAK (TO-263) drawing

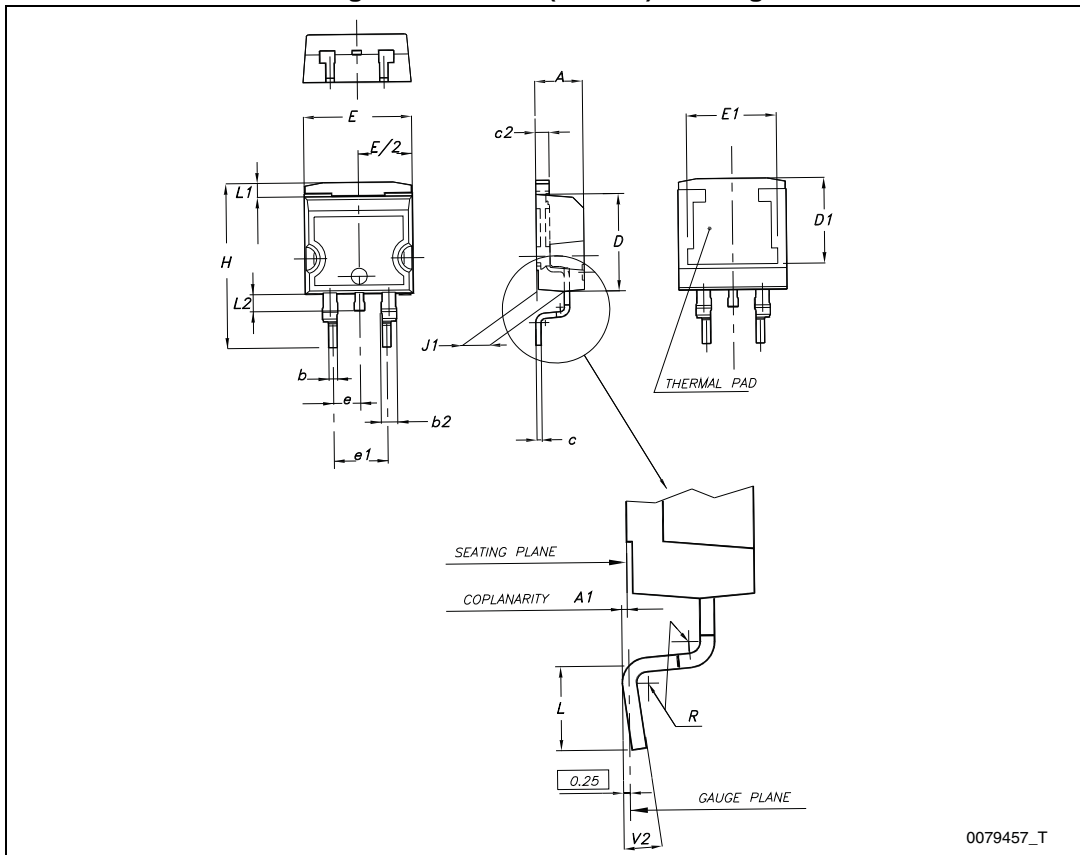
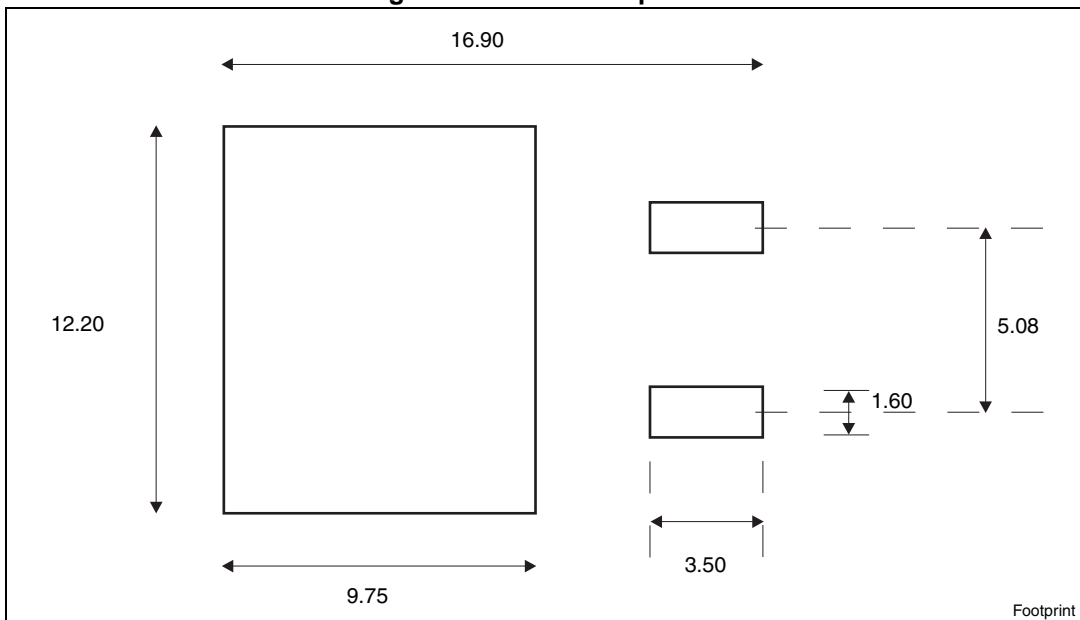


Figure 23. D<sup>2</sup>PAK footprint<sup>(a)</sup>

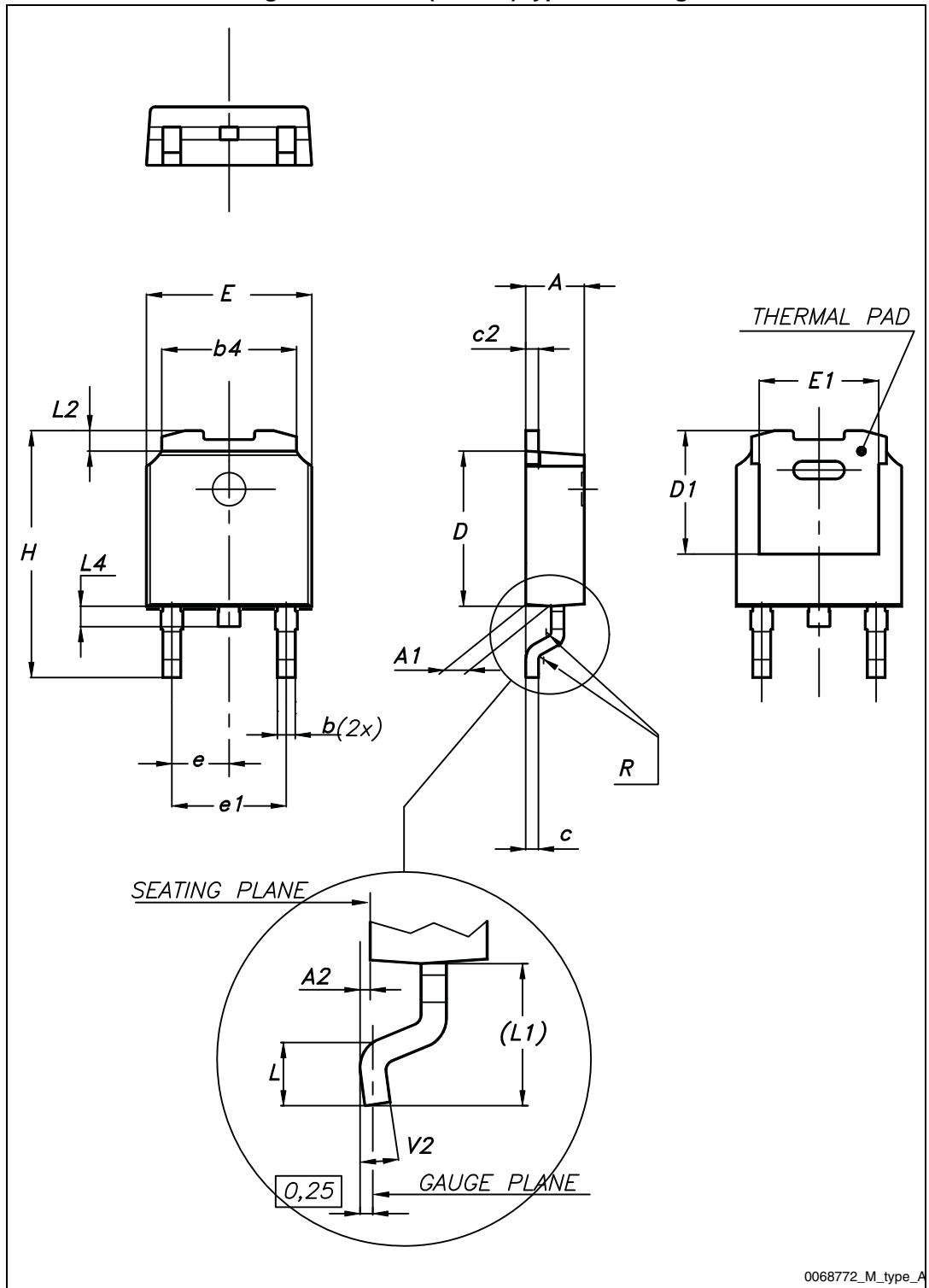


a. All dimension are in millimeters

Table 10. DPAK (TO-252) type A mechanical data

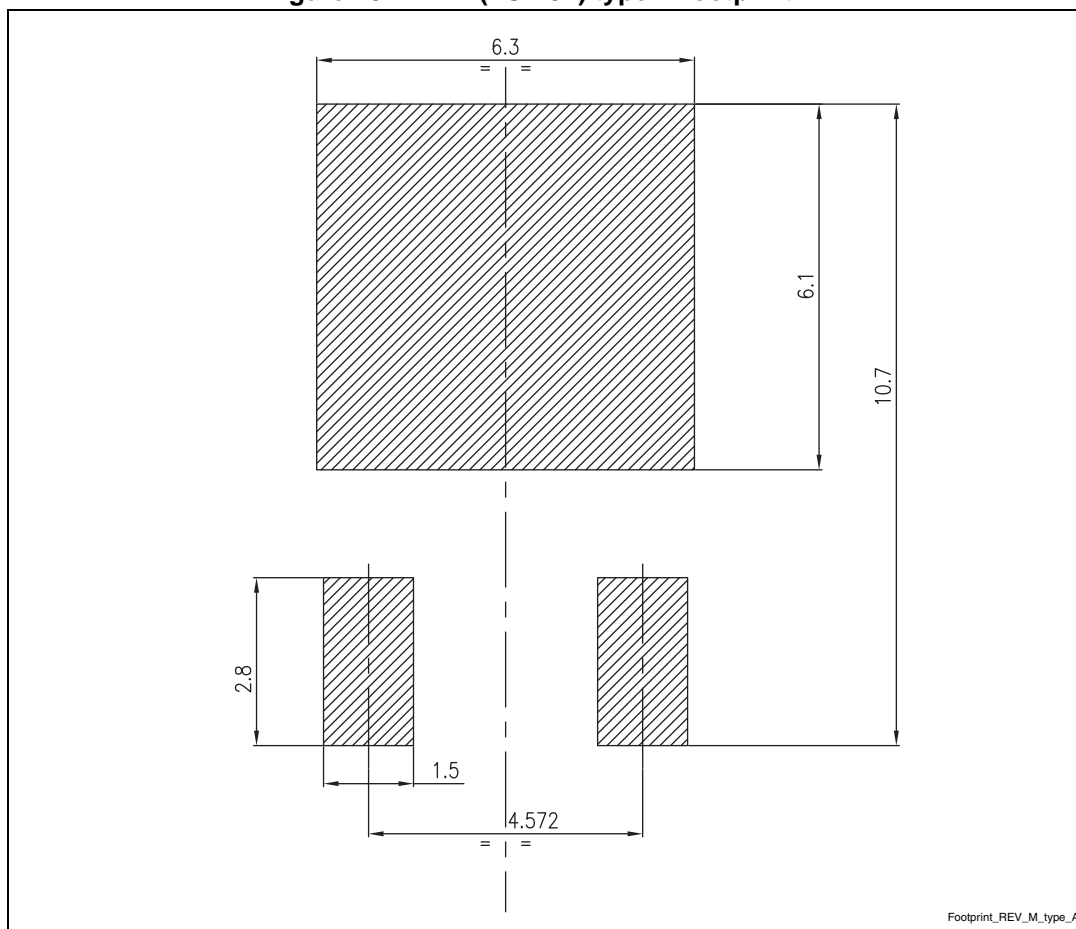
Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 24. DPAK (TO-252) type A drawing



0068772\_M\_type\_A

Figure 25. DPAK (TO-252) type A footprint (b)



b. All dimensions are in millimeters

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



Figure 26. TO-220 type A drawing

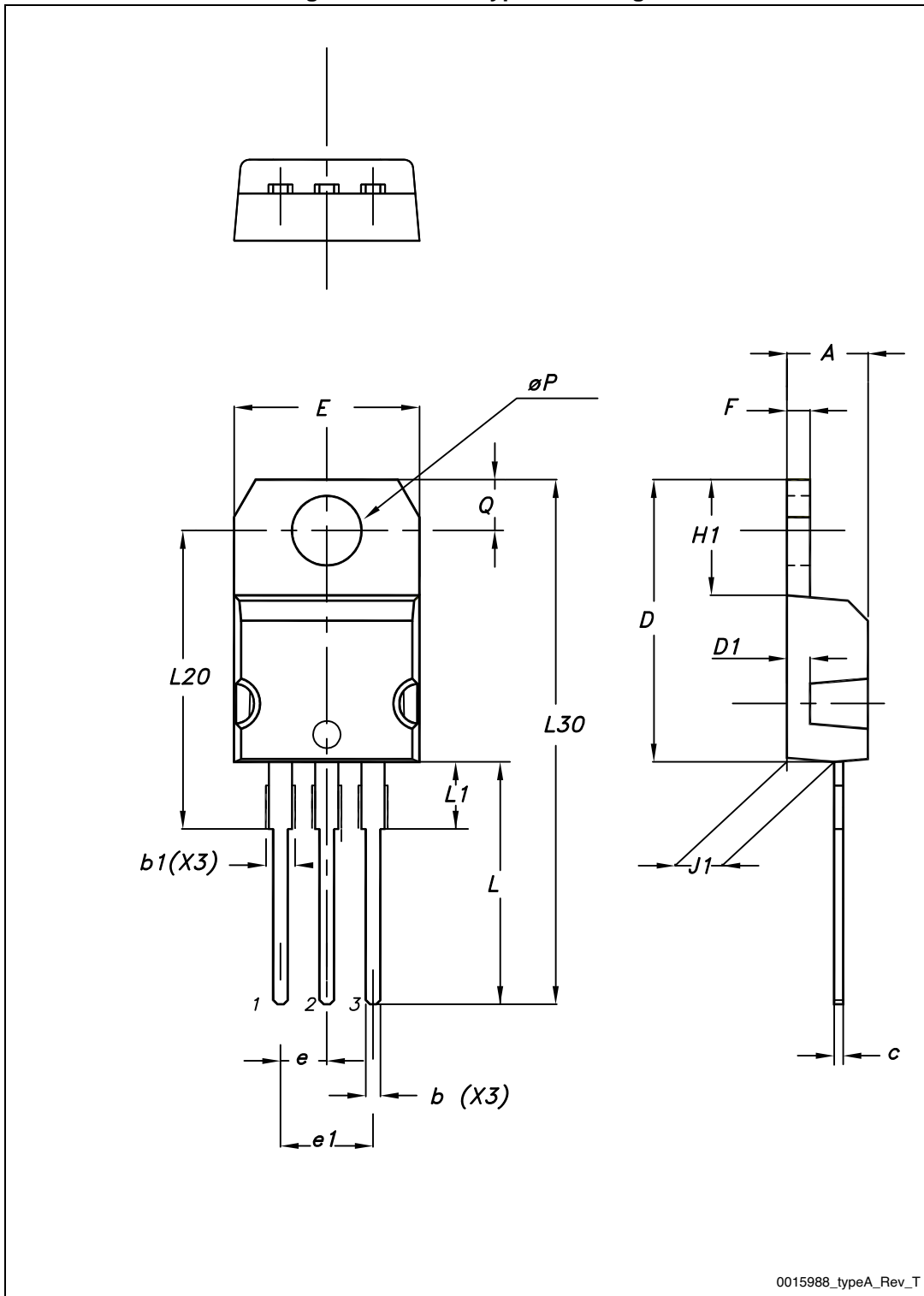
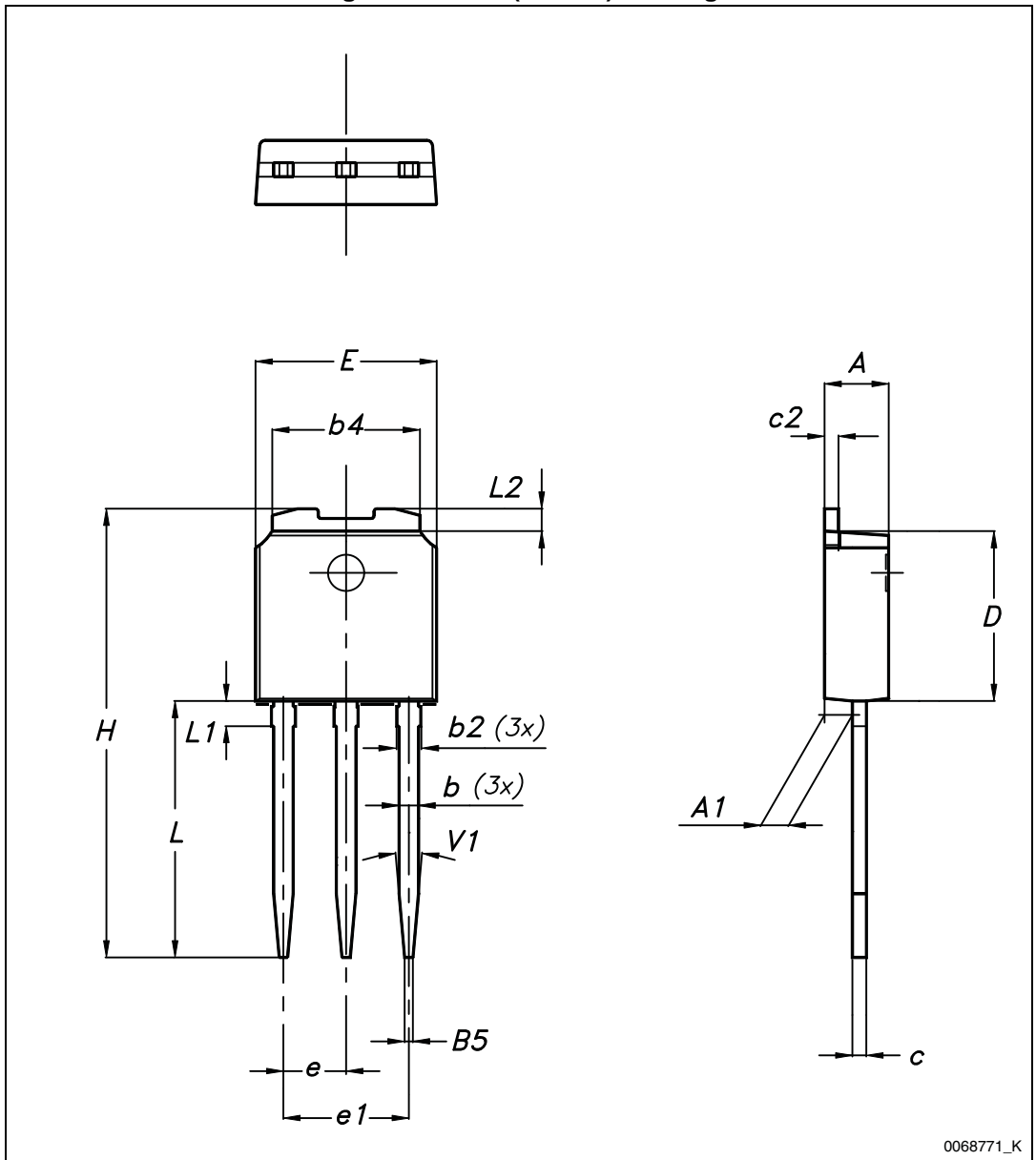


Table 12. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Figure 27. IPAK (TO-251) drawing



0068771\_K

## 5 Packaging mechanical data

Table 13. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 28. Tape for D<sup>2</sup>PAK (TO-263) and DPAK (TO-252)

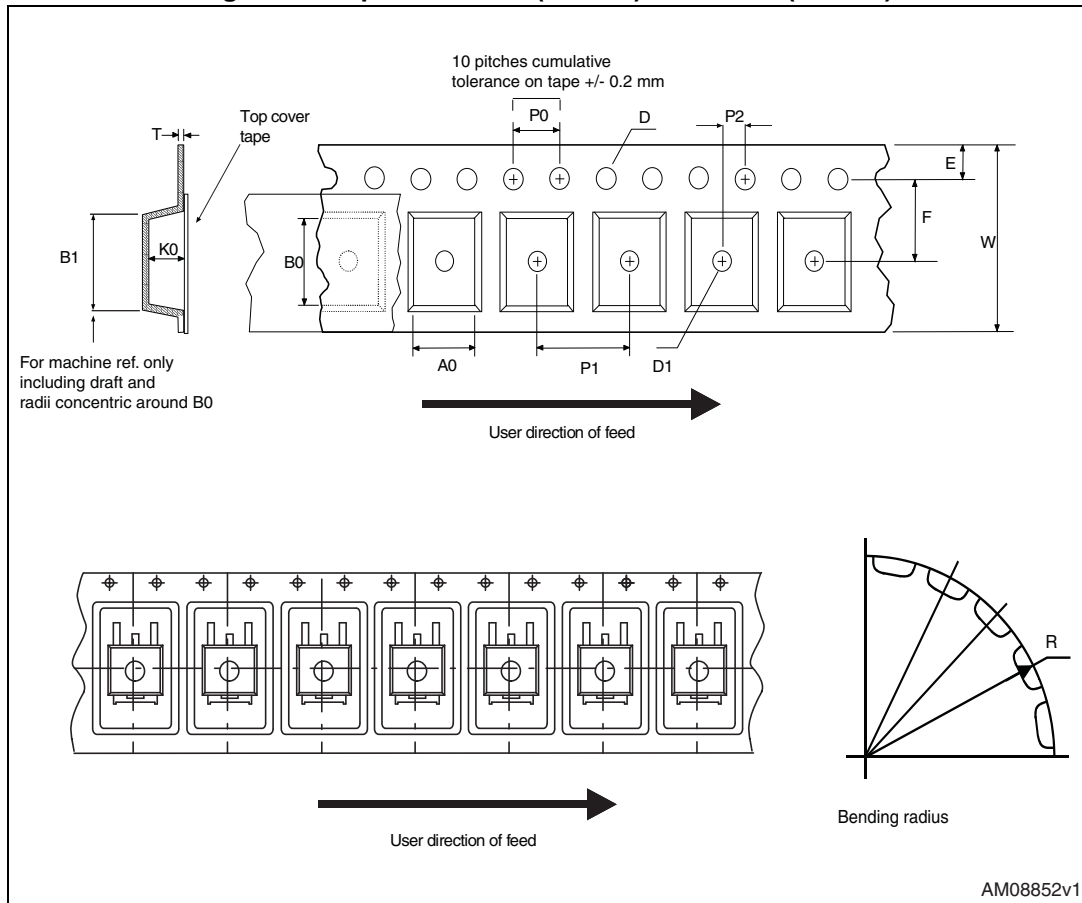
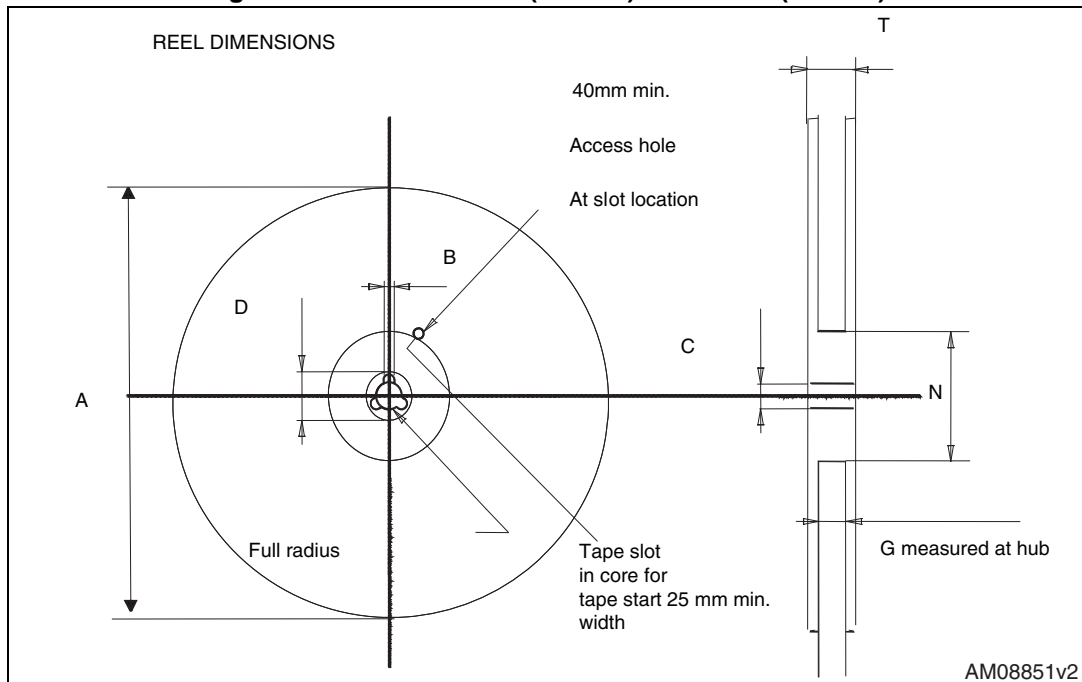


Figure 29. Reel or D<sup>2</sup>PAK (TO-263) and DPAK (TO-252)



## 6 Revision history

Table 15. Document revision history

Date	Revision	Changes
29-May-2013	1	First release.
06-Dec-2013	2	<ul style="list-style-type: none"><li>– Added: D<sup>2</sup>PAK package</li><li>– Modified: title and <math>R_{DS(on)}</math> values in cover page</li><li>– Modified: <math>R_{DS(on)}</math> values in <a href="#">Table 5</a></li><li>– Modified: <math>R_G</math> value in <a href="#">Table 6</a></li><li>– Modified: <a href="#">Figure 9</a> and <math>I_D</math> value in <a href="#">Figure 12</a></li><li>– Added: <a href="#">Table 9, 13, Figure 22</a> and <a href="#">23</a></li><li>– Updated: <a href="#">Table 10, 11, Figure 24, 25</a> and <a href="#">26</a></li><li>– Minor text changes</li></ul>

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